

### Is Now Part of



## ON Semiconductor®

# To learn more about ON Semiconductor, please visit our website at <a href="https://www.onsemi.com">www.onsemi.com</a>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to Fairchild <a href="guestions@onsemi.com">guestions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officer



February 2007

### FDS6294

### 30V N-Channel Fast Switching PowerTrench® MOSFET

#### **General Description**

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low  $R_{\text{DS(ON)}}$  and fast switching speed.

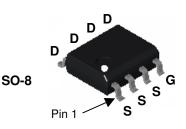
#### **Applications**

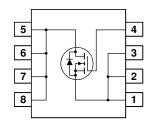
- DC/DC converter
- · Power management
- · Load switch



#### **Features**

- 13 A, 30 V.  $R_{DS(ON)} \, = 11.3 \; m\Omega \; @ \; V_{GS} = 10 \; V$   $R_{DS(ON)} \, = 14.4 \; m\Omega \; @ \; V_{GS} = 4.5 \; V$
- Low gate charge (10 nC typical)
- $\bullet \;\; \mbox{High performance trench technology for extremely} \;\; \mbox{low} \;\; \mbox{R}_{\mbox{\scriptsize DS(ON)}}$
- High power and current handling capability.
- RoHS Compliant





### **Absolute Maximum Ratings** T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		30	V
V <sub>GSS</sub>	Gate-Source Voltage		± 20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	13	Α
	- Pulsed		50	
P <sub>D</sub>	Power Dissipation for Single Operation	(Note 1a)	3.0	W
		(Note 1b)	1.2	
E <sub>AS</sub>	Single Pulse Avalanche Energy	(Note 3)	181	mJ
$T_J$ , $T_{STG}$	Operating and Storage Junction Temperature Range		-55 to +175	°C

#### **Thermal Characteristics**

R <sub>eJA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1b)	125	
R <sub>eJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	25	

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6294	FDS6294	13"	12mm	2500 units

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	1				
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = 250  \mu\text{A}$	30			V
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		27		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			1	μΑ
I <sub>GSS</sub>	Gate-Body Leakage	$V_{GS} = \pm 20 \text{ V},  V_{DS} = 0 \text{ V}$			±100	nA
On Chara	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	1	1.8	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$ , Referenced to 25°C		<b>-</b> 5		mV/°C
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$\begin{split} &V_{GS} = 10 \text{ V}, & I_D = 13 \text{ A} \\ &V_{GS} = 4.5 \text{ V}, & I_D = 12 \text{ A} \\ &V_{GS} = 10 \text{ V}, I_D = 13 \text{ A}, T_J = 125 ^{\circ}\text{C} \end{split}$		9.4 11.5 13.5	11.3 14.4 16.5	mΩ
I <sub>D(on)</sub>	On-State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 5 \text{ V}$	50			Α
<b>g</b> FS	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 13 \text{ A}$		48		S
Dvnamic	Characteristics					•
C <sub>iss</sub>	Input Capacitance	$V_{DS} = 15 \text{ V},  V_{GS} = 0 \text{ V},$		1205		pF
Coss	Output Capacitance	f = 1.0 MHz		323		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			102		pF
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> = 15 mV, f = 1.0 MHz		0.9		Ω
Switchin	g Characteristics (Note 2)					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, \qquad I_D = 1 \text{ A},$		9	18	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, \qquad R_{GEN} = 6 \Omega$		4	8	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			24	48	ns
t <sub>f</sub>	Turn-Off Fall Time			6	12	ns
Qg	Total Gate Charge	$V_{DS} = 15 \text{ V}, \qquad I_{D} = 13 \text{ A},$		10	14	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = 5 \text{ V}$		3.5		nC
$Q_{gd}$	Gate-Drain Charge			3		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source				2.1	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{S} = 2.1 \text{ A (Note 2)}$		0.74	1.2	V
t <sub>rr</sub>	Diode Reverse Recovery Time	$I_F = 13 \text{ A}, d_{iF}/d_t = 100 \text{ A}/\mu\text{s}$		25		nS
Qrr	Diode Reverse Recovery Charge			14		nC

#### Notes

<sup>1.</sup>  $R_{\text{eJA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\text{eJC}}$  is guaranteed by design while  $R_{\text{eCA}}$  is determined by the user's board design.



a) 50 °C/W when mounted on a 1in² pad of 2 oz copper



- b) 125°C/W when mounted on a minimum pad.
- Scale 1:1 on letter size paper

2. Test: Pulse Width < 300μs, Duty Cycle < 2.0%
3. Starting TJ = 25°C, L = 3mH, I<sub>AS</sub> = 11A,V<sub>DD</sub> = 30V, V<sub>GS</sub> = 10V

### **Typical Characteristics**

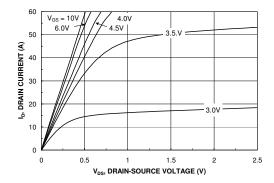


Figure 1. On-Region Characteristics.

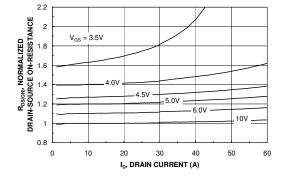


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

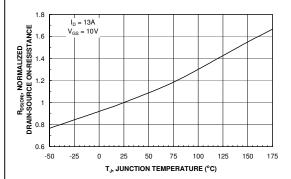


Figure 3. On-Resistance Variation with Temperature.

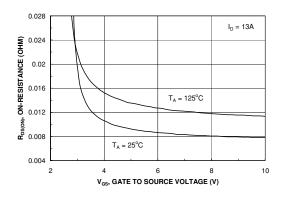


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

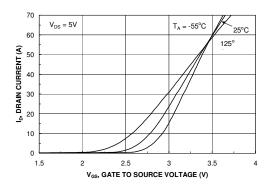


Figure 5. Transfer Characteristics.

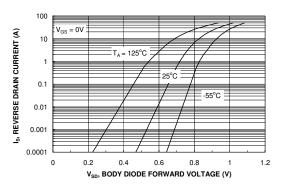
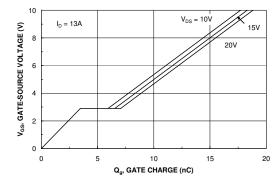


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### **Typical Characteristics**



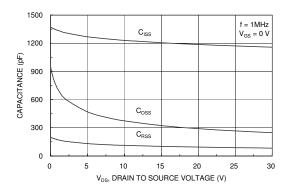
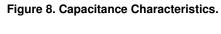
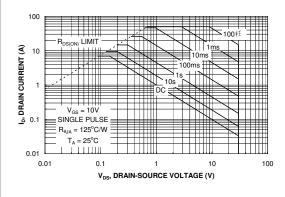


Figure 7. Gate Charge Characteristics.





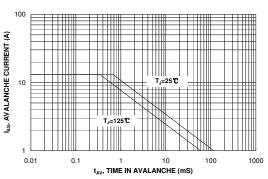
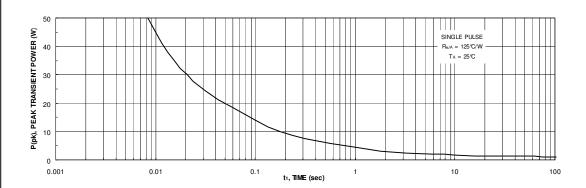


Figure 9. Maximum Safe Operating Area.

Figure 10. Unclamped Inductive Switching Capability Figure



11. Single Pulse Maximum Power Dissipation.



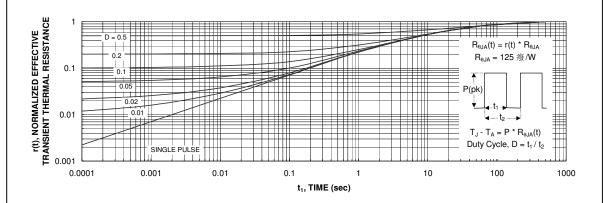


Figure 12. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

#### **TRADEMARKS**

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

**ACEx™** FACT Quiet Series™  $OCX^{TM}$ SILENT SWITCHER® UniFET™ ActiveArray™ OCXPro<sup>™</sup> SMART START™ **VCX™** GlobalOptoisolator™ OPTOLOGIC® Bottomless™ GTO™ SPM™ Wire™ HiSeC™ OPTOPLANAR™ Build it Now™ Stealth™ CoolFET™  $\mathsf{PACMAN^{\mathsf{TM}}}$ SuperFET™ I<sup>2</sup>C™ РОР™ SuperSOT™-3 CROSSVOLT™ i-Lo<sup>TM</sup> DOME™ ImpliedDisconnect™ Power247™ SuperSOT™-6 PowerEdge™ EcoSPARK™ IntelliMAX™ SuperSOT™-8 E<sup>2</sup>CMOS™ ISOPLANAR™ PowerSaver™ SyncFET™ EnSigna™ LittleFET™ PowerTrench® ТСМ™ QFET<sup>®</sup> FACT<sup>®</sup> MICROCOUPLER™ TinvBoost™  $\mathsf{FAST}^{\mathbb{R}}$ QS<sup>TM</sup> TinyBuck™ MicroFET™ MicroPak™  $\mathsf{TinyPWM}^{\mathsf{TM}}$ FASTr™ QT Optoelectronics™ TinyPower™ FPS™ MICROWIRE™ Quiet Series™ FRFET™ RapidConfigure™ MSX<sup>TM</sup> TinyLogic<sup>®</sup> MSXPro™ RapidConnect™ TINYOPTO™ Across the board. Around the world.™ µSerDes™ TruTranslation™ **UHC®** The Power Franchise® ScalarPump™

#### DISCLAIMER

DISCLAIMEN
FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS
HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE
APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS
PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S
WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

#### LIFE SUPPORT POLICY

Programmable Active Droop™

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.

2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

#### PRODUCT STATUS DEFINITIONS **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. 122

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hol

#### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative